

Claim

in that order beginning with the silicon layer.

4. (Amended) A semiconductor device according to Claim 1, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

C²

5. (Twice Amended) A semiconductor device with an MOS transistor whose gate electrode is provided as a stacked structure comprising a silicon layer and a metallic layer as the uppermost layer thereof, wherein a metal silicide layer is provided on the silicon layer side and a metal nitride layer is provided under the metallic layer side between the silicon layer and the metallic layer.

C³

8. (Amended) A semiconductor device according to Claim 5, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer and the metallic layer is a tungsten layer.

C⁴

25. (Amended) A semiconductor device with complementary MOS transistors, each MOS transistor having a gate electrode, a source region and a drain region, wherein the gate electrode is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed in that order beginning with the silicon layer.

C⁵

28. (Amended) A semiconductor device according to claim 25, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

C⁶

6
Cmcdi

29. (Amended) A semiconductor device with complementary MOS

transistors, each MOS transistor having a gate electrode, a source region and a drain region, wherein the gate electrode is provided as a stacked structure comprising a silicon layer, an uppermost metallic layer, a metal silicide layer provided on the silicon layer side and a metal nitride layer provided under the metallic layer side between the silicon layer and the metallic layer.

C

31. (Amended) A semiconductor device according to claim 29, wherein the

metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

6⁸

33. (Amended) A semiconductor device comprising on a substrate, at least

one MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed in that order beginning with the silicon layer.
